

# Micro-solid oxide fuel cells running on reformed hydrocarbon fuels

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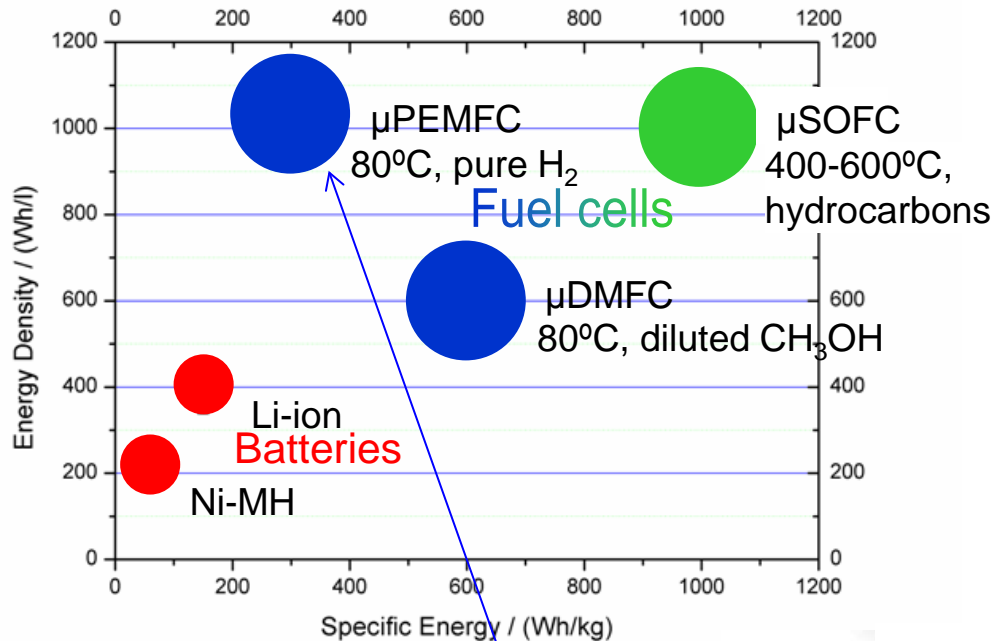
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## Sources for mobile energy



Horizon Minipack is a recharging system based on PEMFC

<http://www.horizonfuelcell.com>



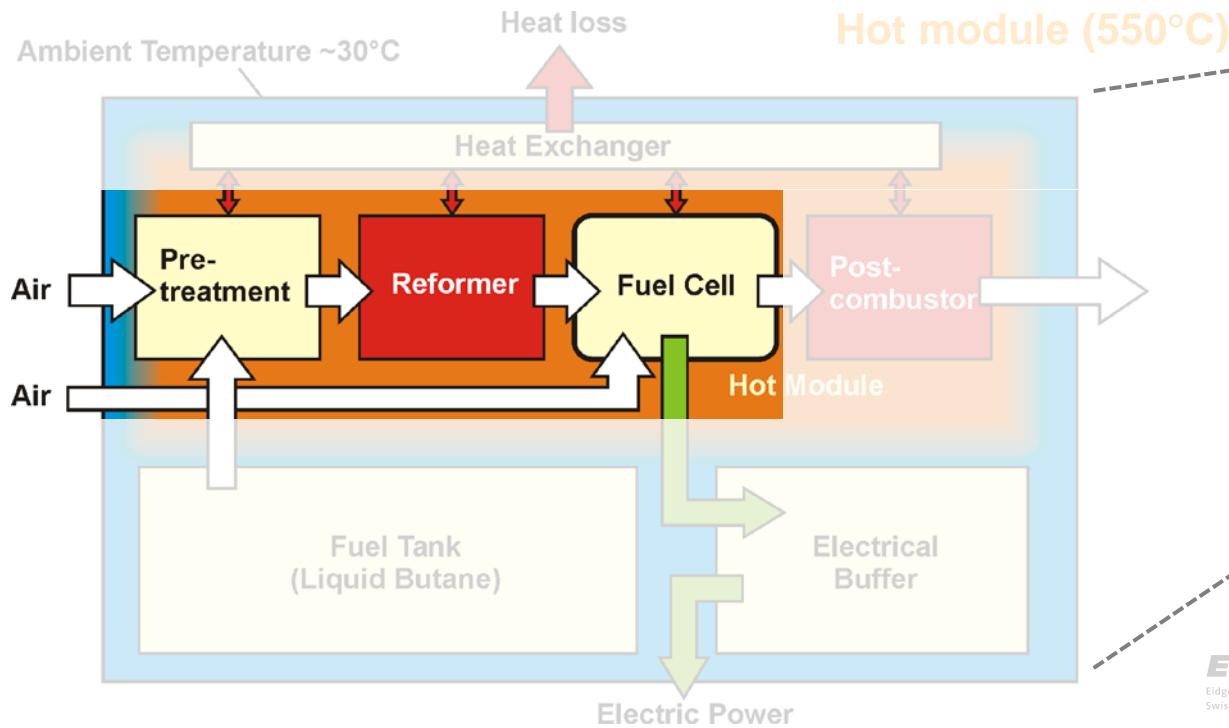
### Advantages of micro-SOFC:

- high efficiency
- high energy density
- fuel flexibility
- geographically independent

### Challenges of micro-SOFC:

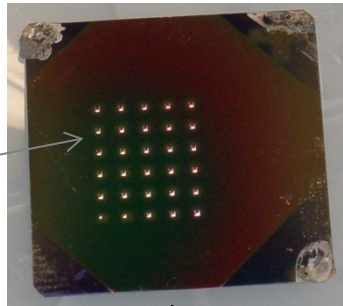
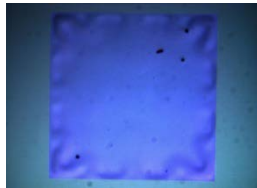
- high temperature

# Micro-fuel cell systems for battery replacement

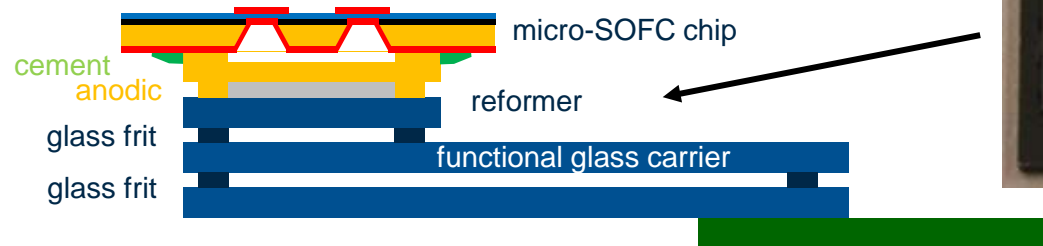
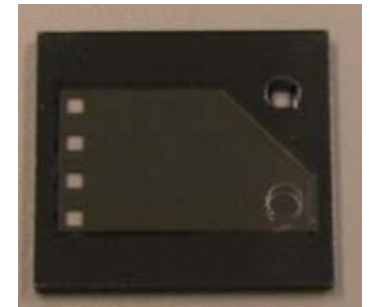


# Assembly of glass carrier, reformer and micro-SOFC chip

micro-SOFCs on Si chip  
(Pt/YSZ/Pt)



micro reformer  
(2 wt% Rh/Ce<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>)



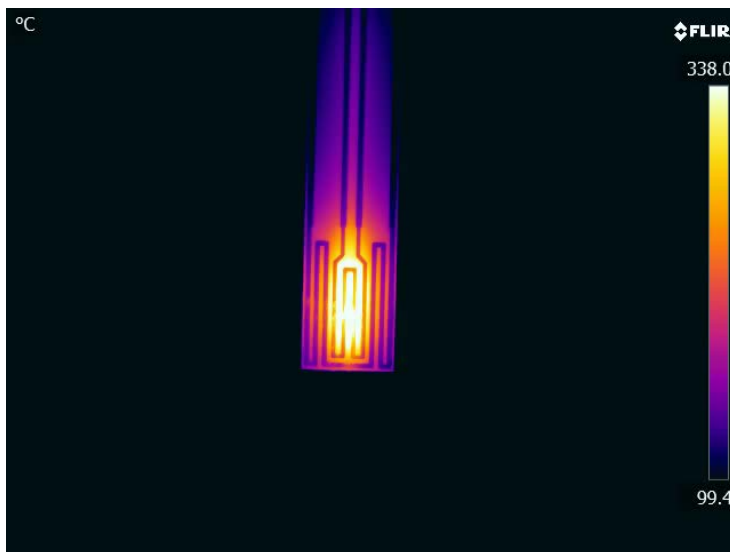
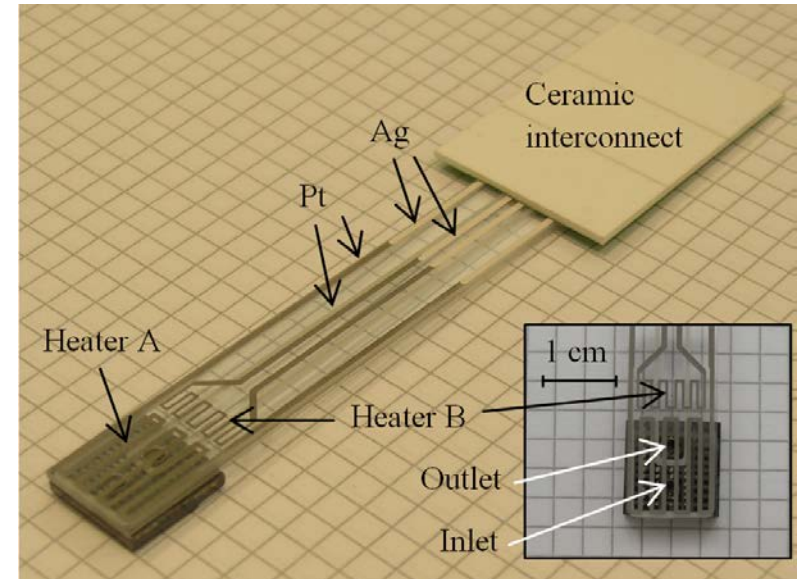
functional glass carrier



(gas supply and heater)

## Functional glass carrier

- Fabrication of carrier:
  - Schott AF 32®
    - $T_G = 717\text{ °C}$
  - Glass frit bonding
    - $H = 100\text{ }\mu\text{m}$

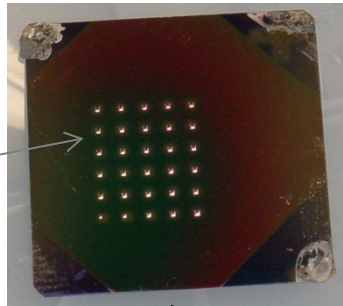
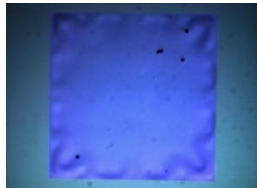


- Fabrication of heaters:
  - Pt and Ag heaters
  - Screen printed heaters
    - Height <math>< 50\text{ }\mu\text{m}</math>
  - Heater A: bottom of MR
  - Heater B: before MR inlet

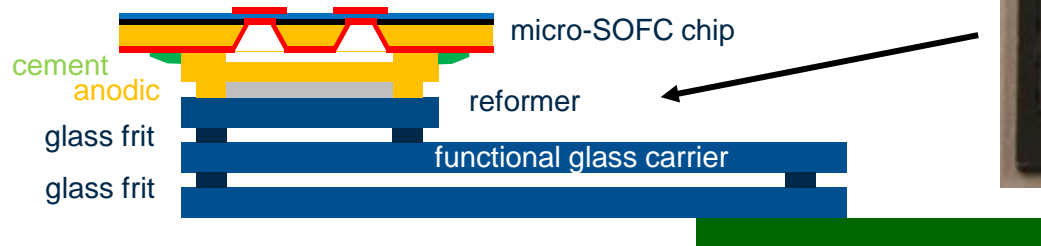
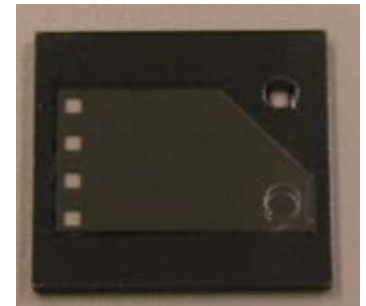


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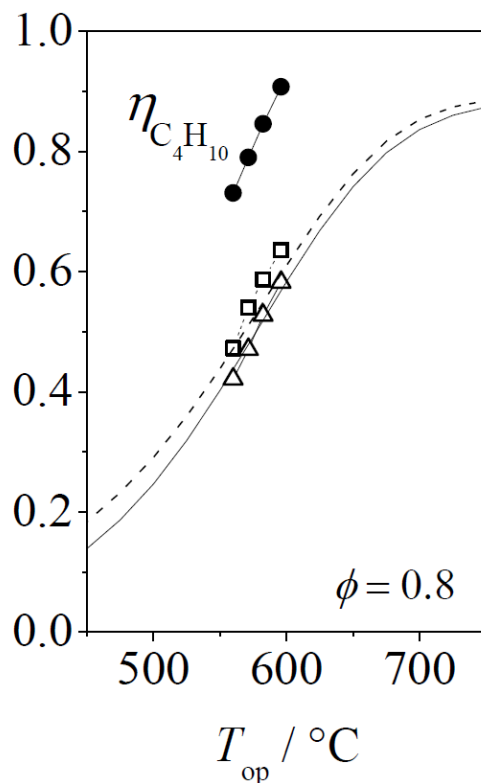


(gas supply and heater)

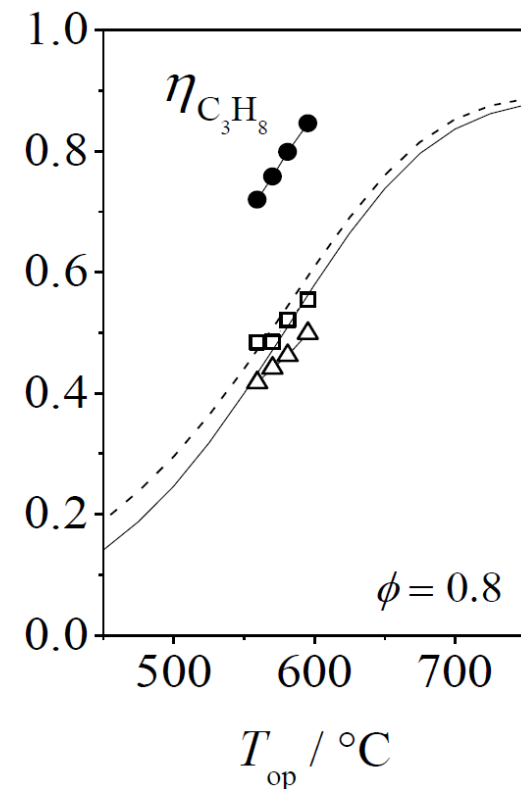
## Micro reactor

- Conversion of  $C_4H_{10}$  is higher
- $H_2$  production from  $C_4H_{10}$  is higher
- n-Butane: C/O = 0.7 and C/O = 0.8 are best dilutions
- Propane: C/O = 0.8 is best dilution

n-Butane



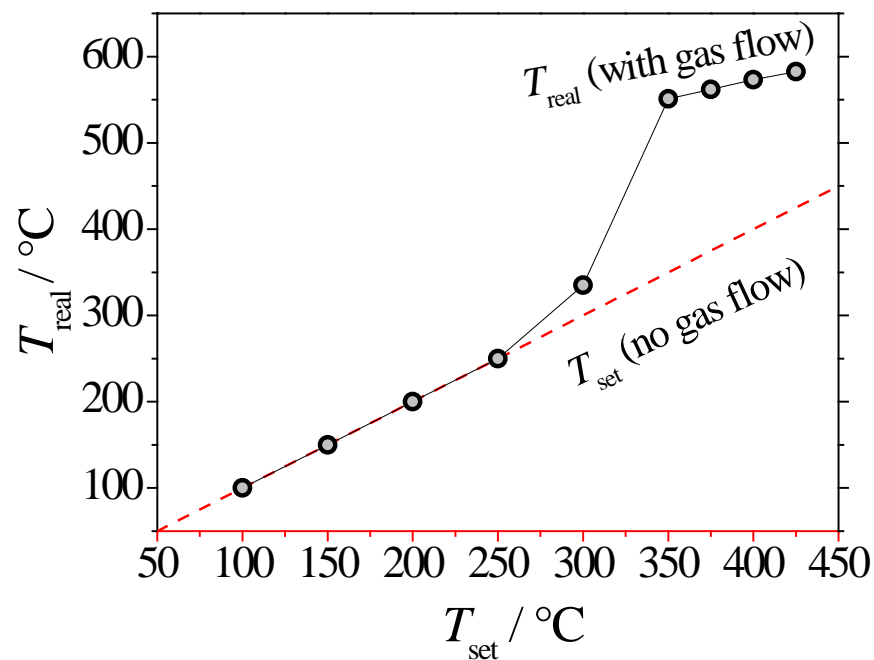
Propane



	$\phi$		$C_xH_y$ -species		Syngas-species		
			$\eta$	$x_{CH_4}$	$\psi_{H_2}$	$\psi_{CO}$	$\psi_{syngas}$
n-Butane	0.7	Average $\pm \sigma$ [%]	95.2 $\pm$ 0.1	0.18 $\pm$ 0.0	66.7 $\pm$ 0.4	51.7 $\pm$ 0.5	60.1 $\pm$ 0.5
		Outlet flow rate [ $\mu$ mol/s]	0.06 $\pm$ 0.01	0.24 $\pm$ 0.01	4.43 $\pm$ 0.14	2.74 $\pm$ 0.11	7.17 $\pm$ 0.13
Propane	0.8	Average $\pm \sigma$ [%]	84.3 $\pm$ 0.4	0.16 $\pm$ 0.0	55.4 $\pm$ 0.1	42.5 $\pm$ 0.1	49.8 $\pm$ 0.1
		Outlet flow rate [ $\mu$ mol/s]	0.31 $\pm$ 0.01	0.32 $\pm$ 0.01	4.33 $\pm$ 0.01	2.50 $\pm$ 0.01	6.83 $\pm$ 0.01

## Micro reactor

- Temperature increase behavior during testing
  - Reaction starts > 300 °C
- Higher flow rate results in higher temperature.

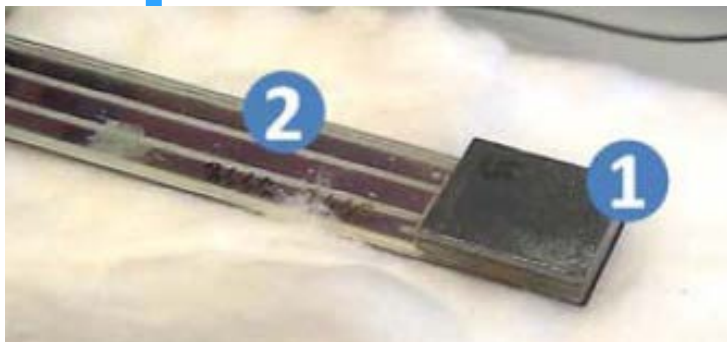




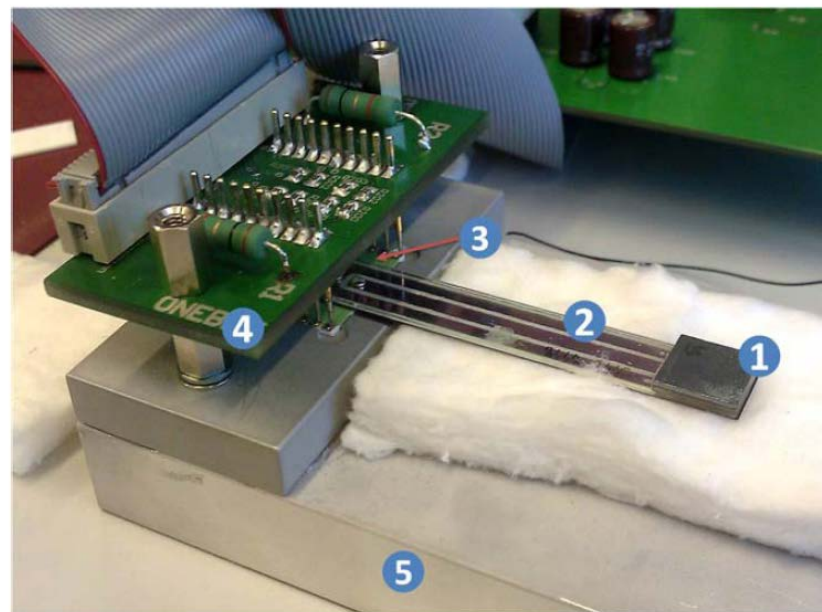
## Characterization of micro reformer

... in the furnace

Furnace

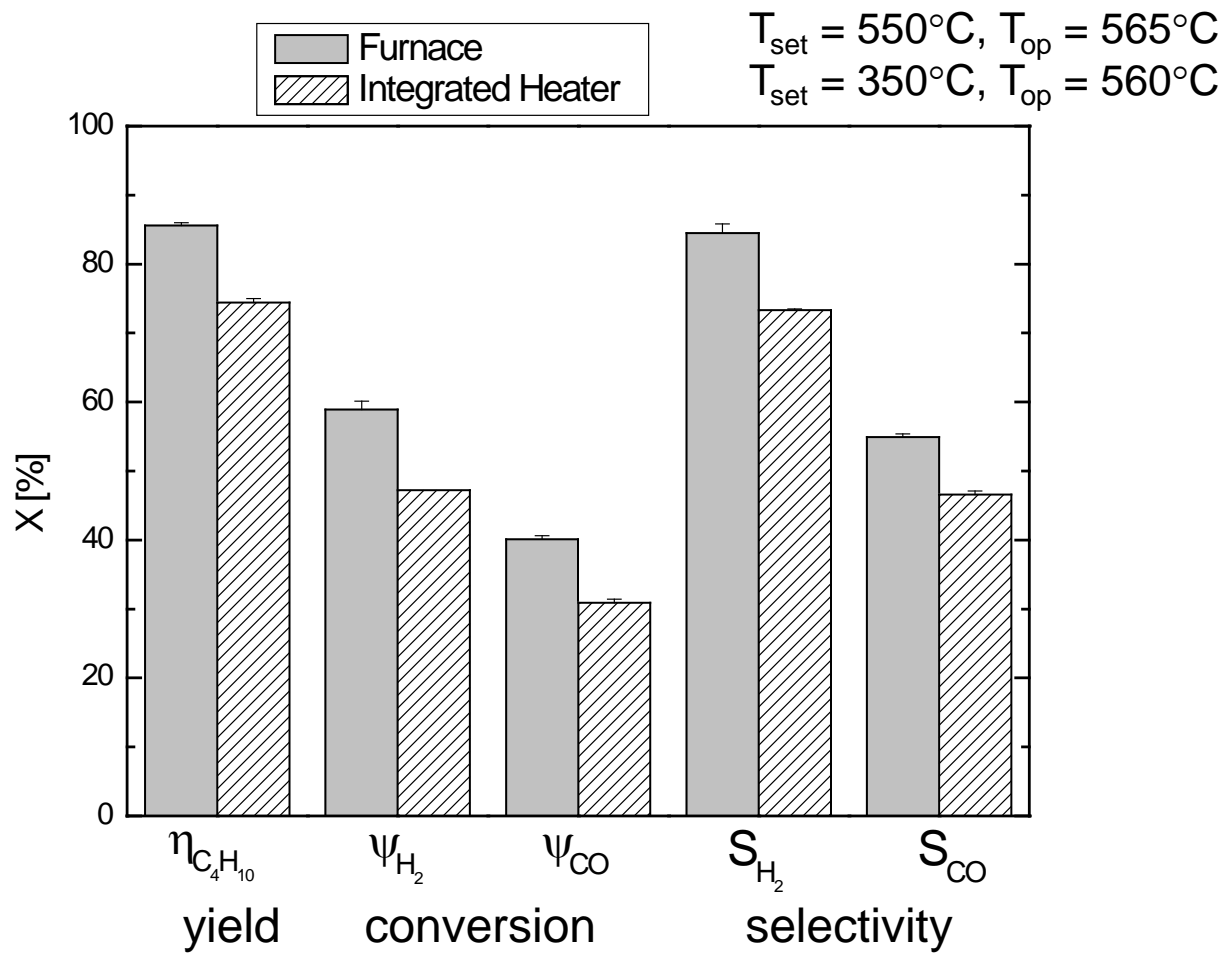


... on the carrier with integrated heaters



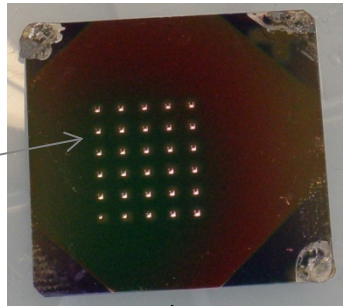
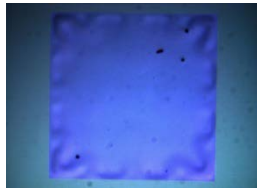
## Results of gas analysis

- Less even temperature distribution results in lower yield, conversion and selectivity for the integrated heater setup.
- Better insulation will improve it again.

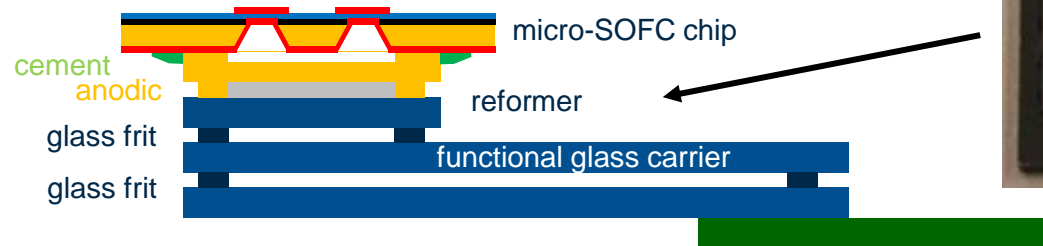
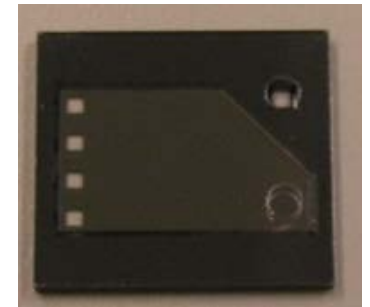


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(2 wt% Rh/Ce<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>)



functional glass carrier



(gas supply and heater)

# Micro-SOFC fabrication

Si Wafer (380  $\mu\text{m}$ ), LPCVD-Si<sub>3</sub>N<sub>4</sub> (200 nm) on both sides



Window opening (900  $\mu\text{m}$ ): photolitho + RIE of Si<sub>3</sub>N<sub>4</sub>



Si wet etching: KOH 20%, 90 °C



YSZ deposition: AA-CVD, PLD, spray pyrolysis



Release of the YSZ membrane by reactive ion etching



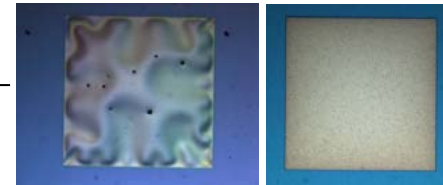
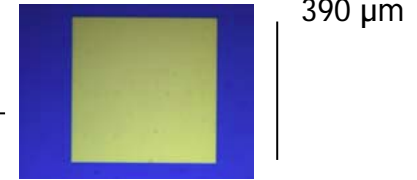
Top-side electrode deposition



Back-side electrode deposition



Top-view light micrographs

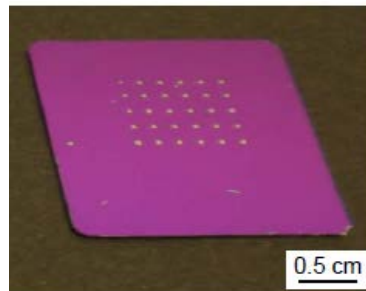


comp.  
stress

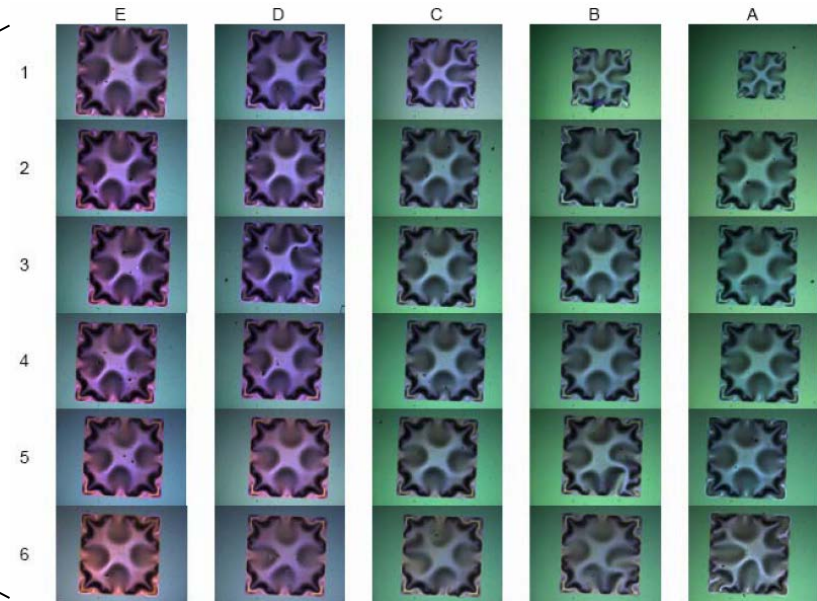
tens.  
stress



# Micro-SOFC fabrication



Test chip

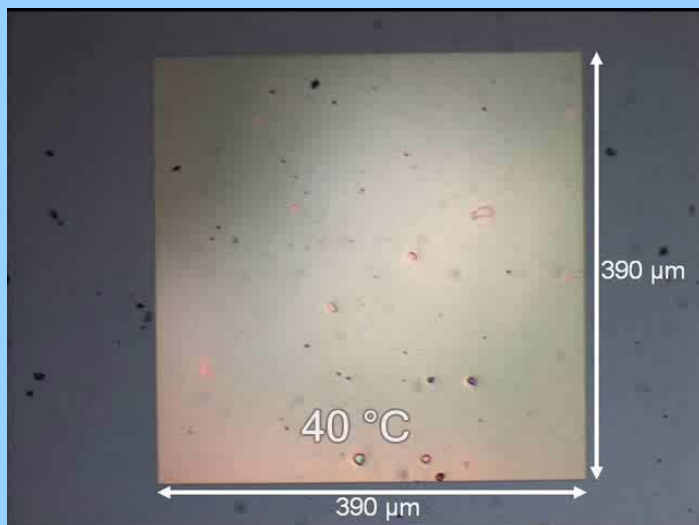


membrane side length: 390  $\mu\text{m}$

- Test chip: 30 free-standing micro-SOFC membranes
- Membrane yield (%):  $\text{number of surviving membranes} / 30 * 100$
- Membrane yield target:  $\sim 100\%$

## Thermomechanical stress

$T_{\text{dep}} = 25\text{ °C}$

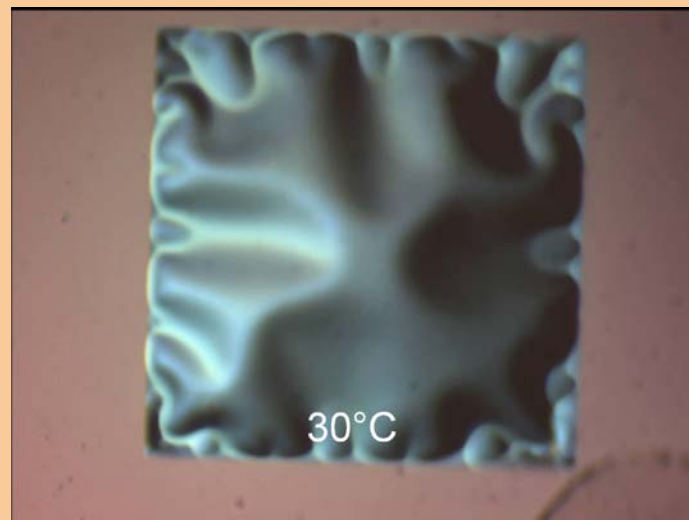


Partially crystalline as-deposited film (PLD)

Yield after free-etching: ca. 100%

Tensile stress (flat membrane)

$T_{\text{dep}} = 700\text{ °C}$



Fully crystalline as-deposited film (PLD)

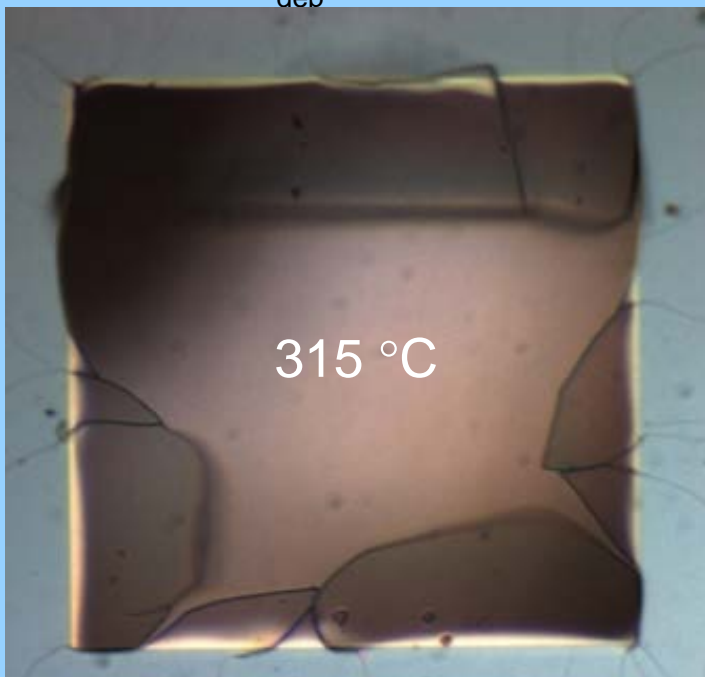
Yield after free-etching: ca. 100%

Compressive stress (buckled membrane)



## Thermomechanical stress

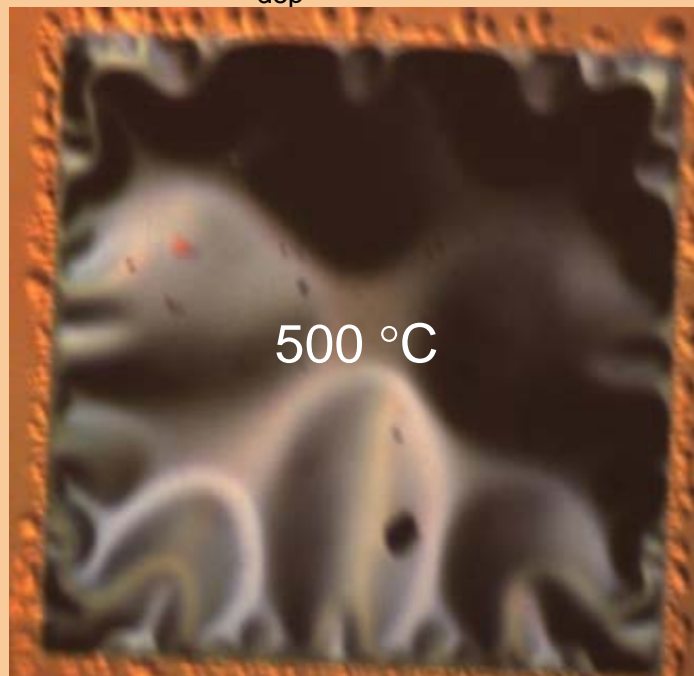
$T_{\text{dep}} = 25\text{ °C}$



Crystallization during heating  $\gg$  tensile stress

Membrane rupture (low yield:  $< 10\%$ )

$T_{\text{dep}} = 700\text{ °C}$



Buckling «apparently» unchanged during heating

Robust membrane (high yield:  $100\%$ )

## Residual stress in free-standing YSZ membranes

PLD  $T_{\text{depo}}$

free-standing membrane  
(390x390  $\mu\text{m}^2$  300nm  
8YSZ)

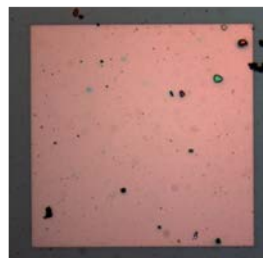
Yield:

after deposition

after annealing at 500 °C

SAMLAB

25°C



98%

0%

--

400°C

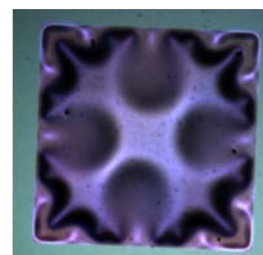


0%

0%

-2.1 GPa

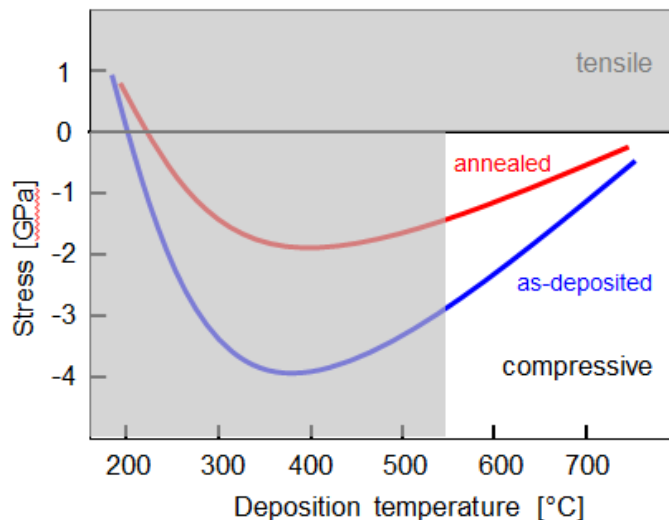
700°C



>99%

>99%

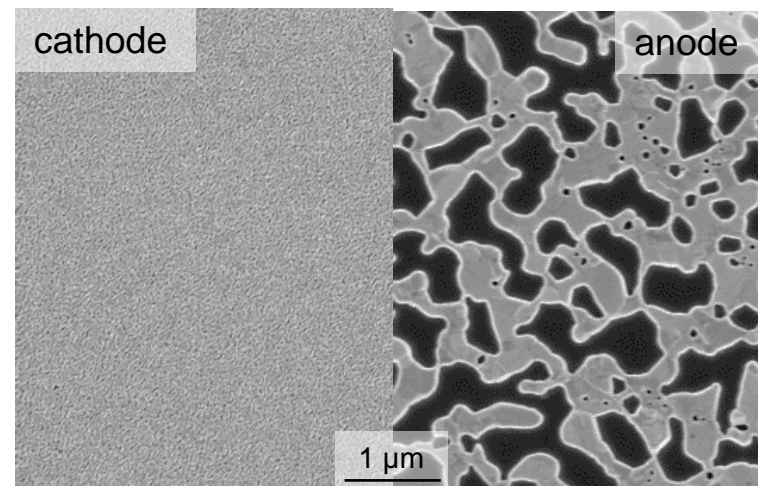
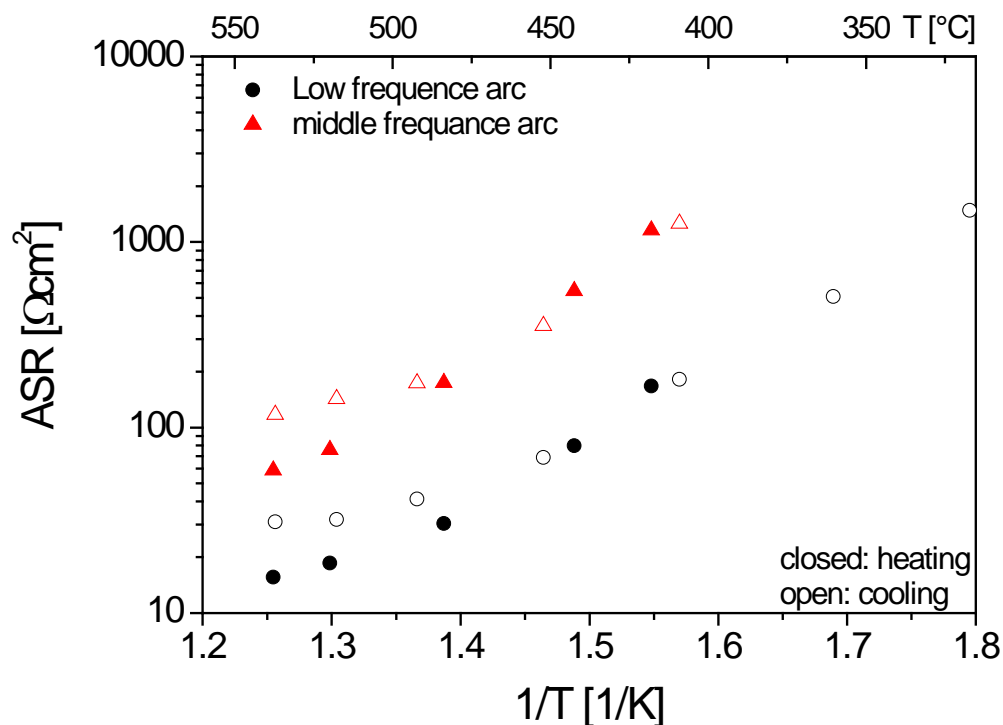
-1.4 GPa



Different stresses  $f(T_{\text{depo}})$ :

- Tensile and too much compressive stress result in membrane rupture.

## ASR of Pt in fuel cell conditions



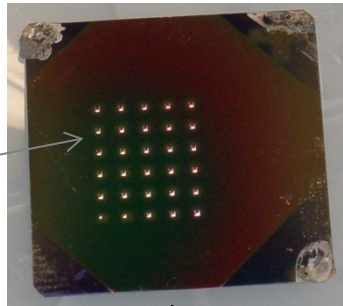
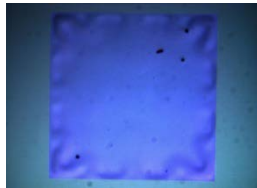
cathode: 300 sccm air  
anode: 60 sccm H<sub>2</sub> in 240 sccm N<sub>2</sub>

Pt thin films tested on YSZ single crystal

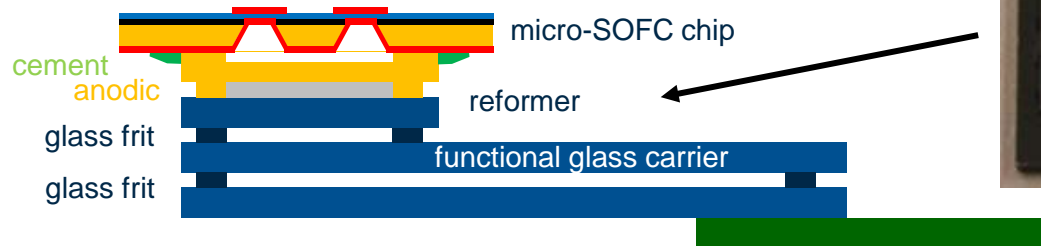
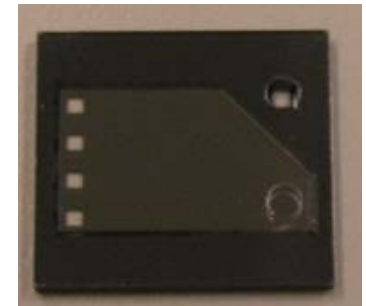
- ASR of the electrodes are stable over heating and cooling
- Microstructure is different depending on the seen environment

# Assembly of glass carrier, reformer and micro-SOFC chip

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(2 wt% Rh/Ce<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>)



functional glass carrier



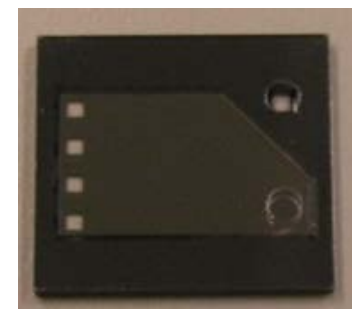
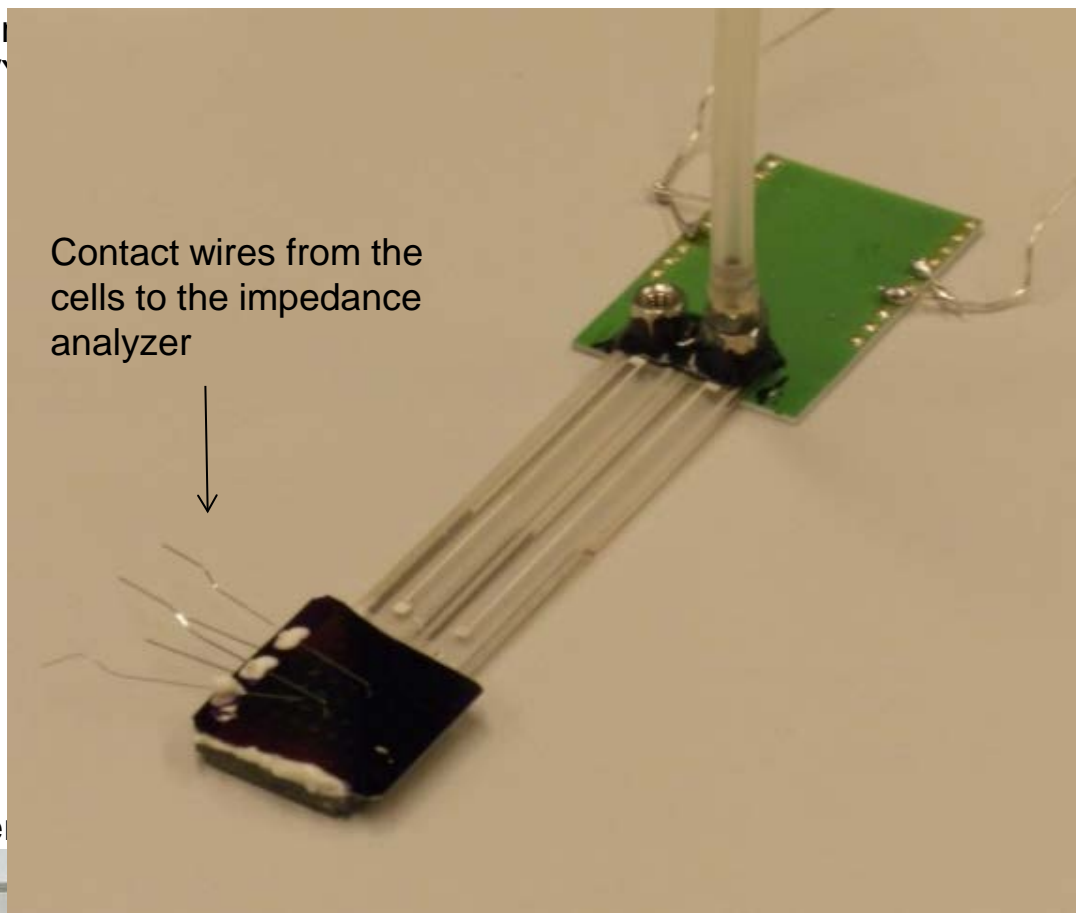
(gas supply and heater)

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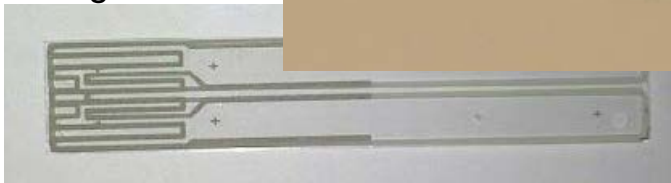
micro  
(Pt/

Contact wires from the cells to the impedance analyzer

micro reformer  
(2 wt% Rh/Ce<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>)



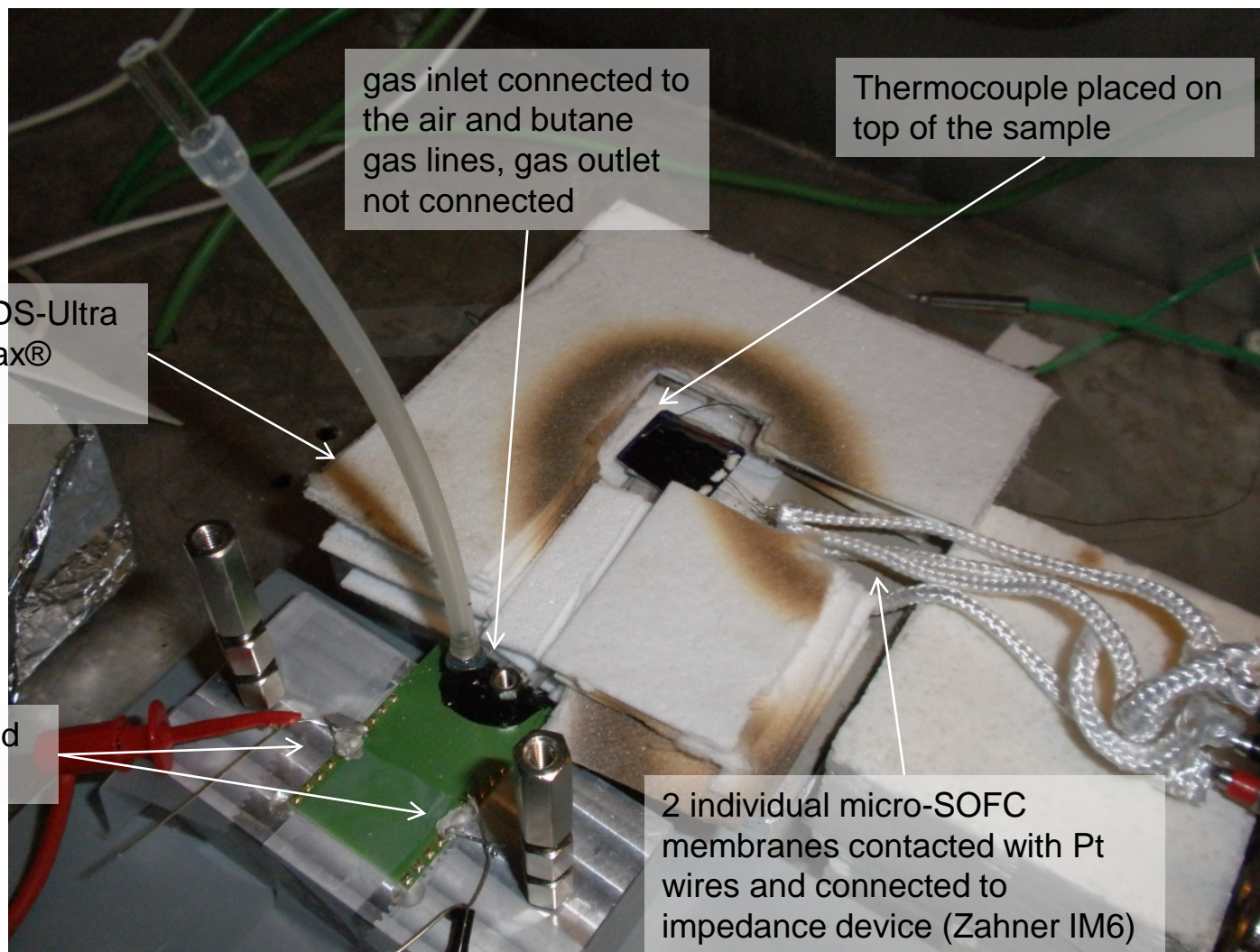
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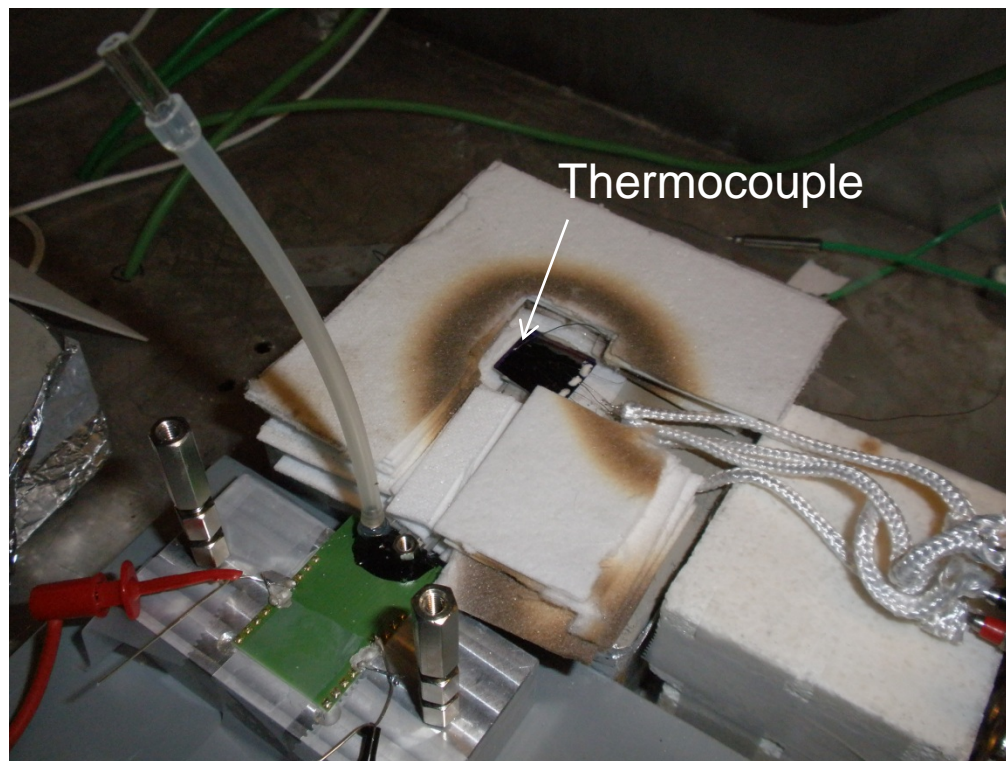
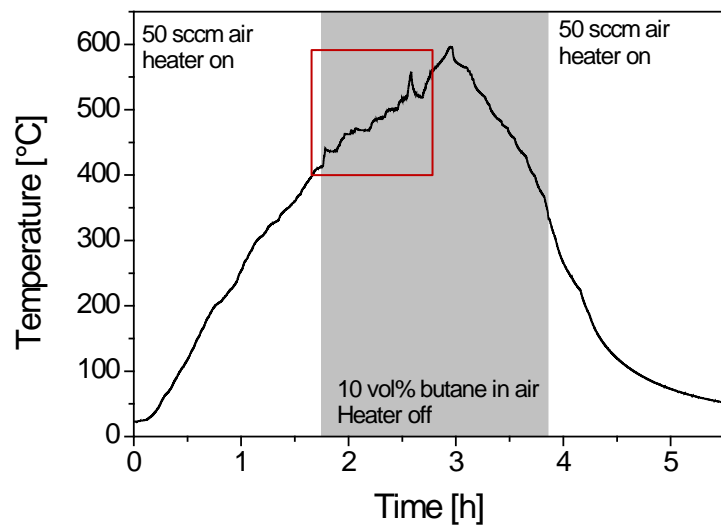


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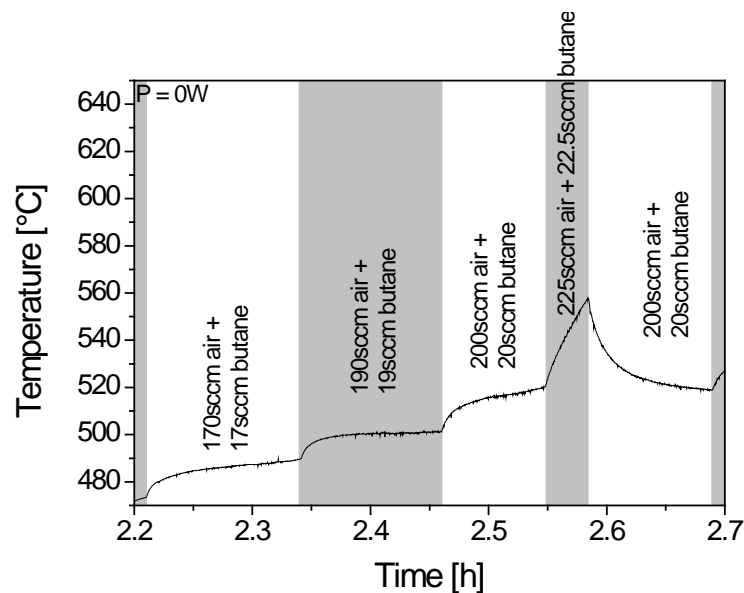
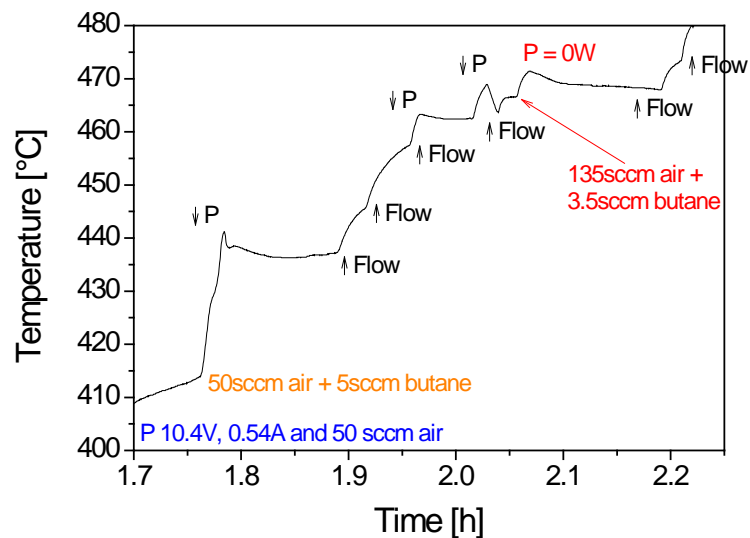


## Temperature program



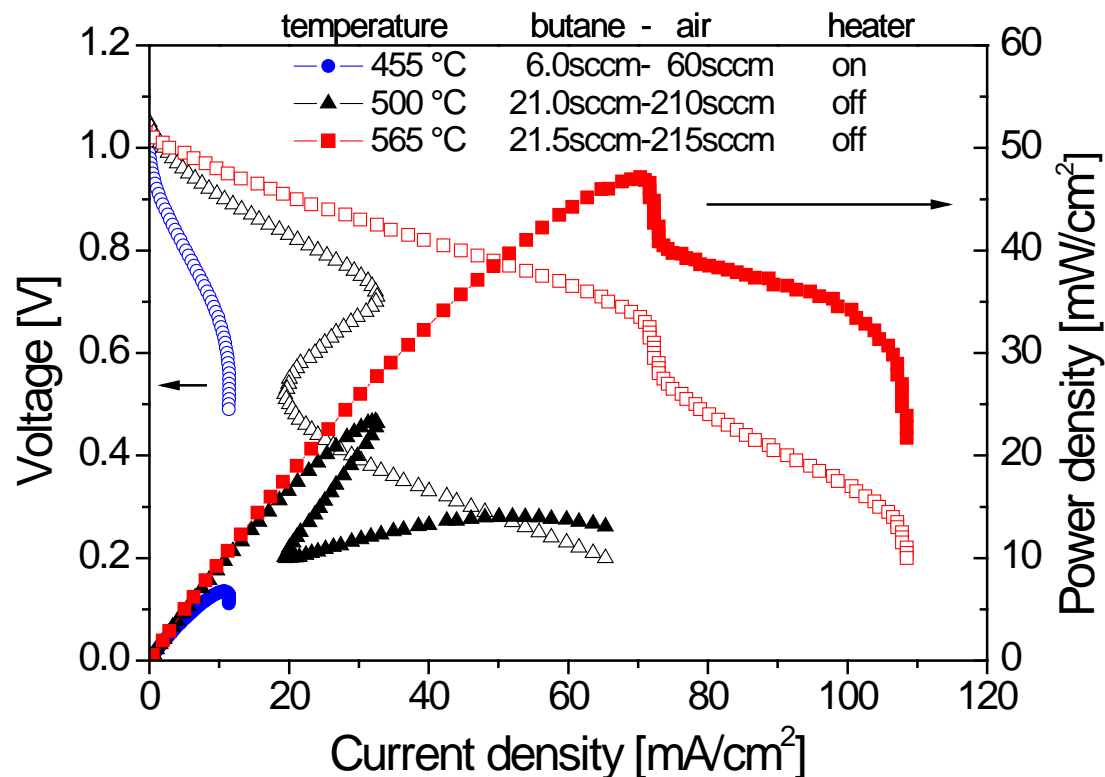
- Heating ramp done by increasing voltage
- Temperature measurement on the sample is accurate

## Temperature program

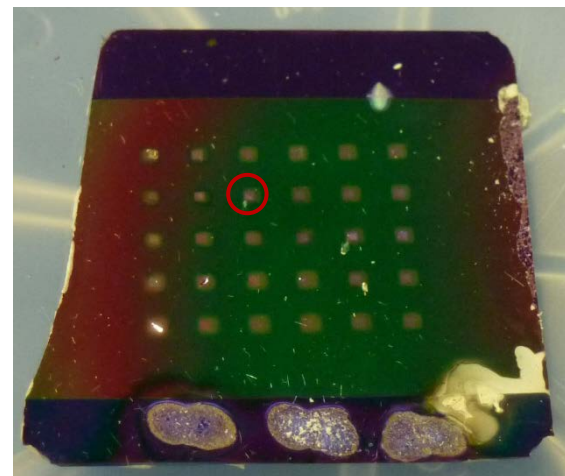


- Self sustained reaction of the reformer heats the assembly further
  - Increasing flow results in increasing temperature
- Almost stable temperature reached after 2 min

## Cell voltage and power density

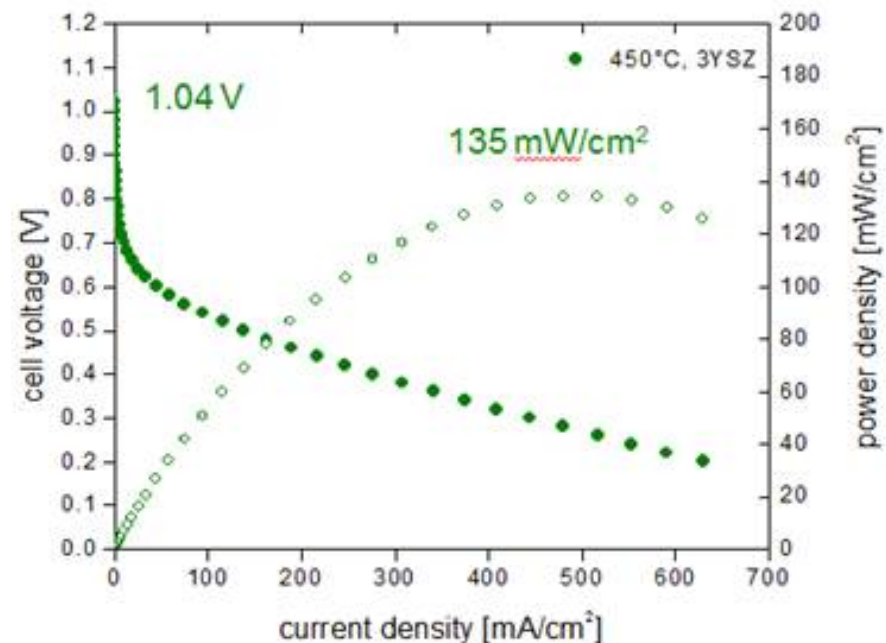
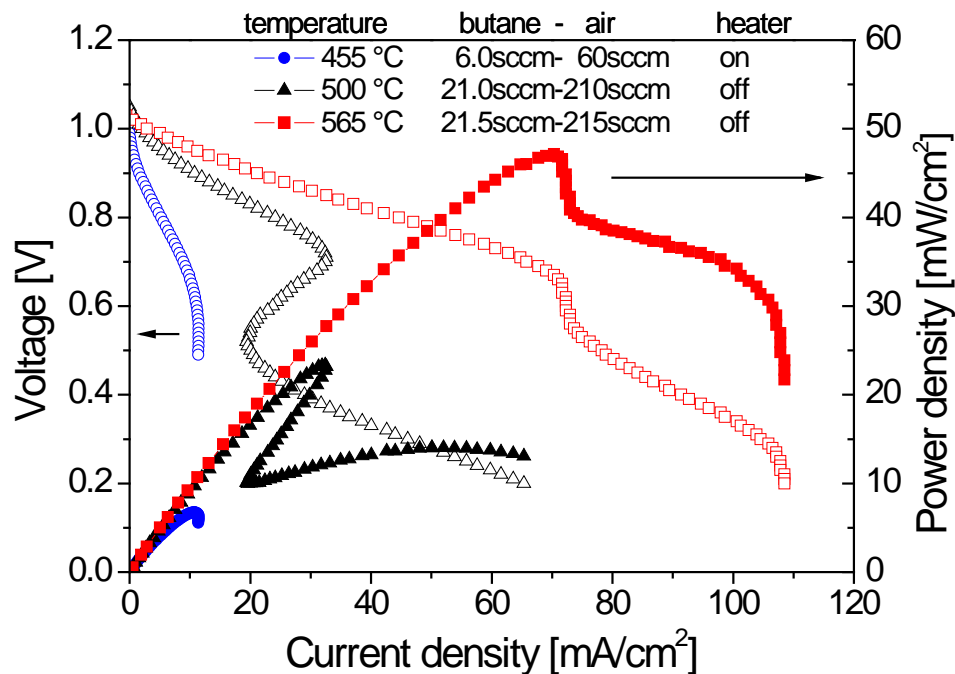


After testing



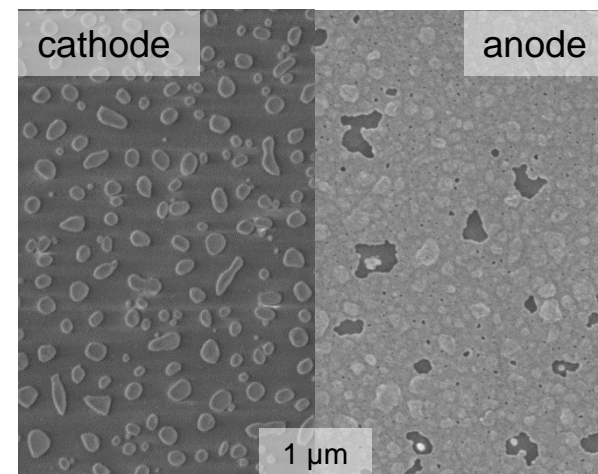
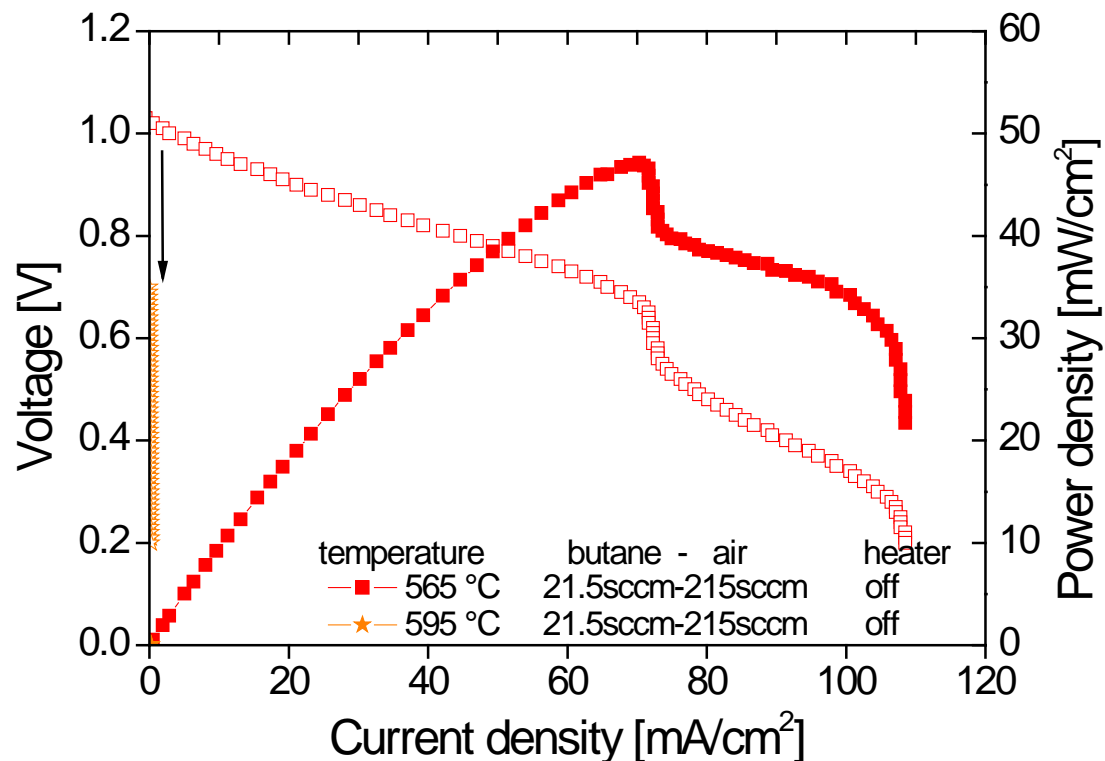
- Theoretical open circuit voltage was achieved!
  - Gas-tight membranes
- Maximum power density of about 50 mW/cm<sup>2</sup> at 565 °C!
- All membranes survived the testing program (maximal temperature of 596 °C)!

## Cell voltage and power density – comparison



- Strange curve shape at ~0.7 V, most likely due to excess water at the gas outlet.

## Cell voltage and power density – decrease in OCV



- Long-term testing not possible due to instable Pt-electodes
  - Cathode agglomerates more severe most likely due to the surface roughness of the electrolyte layer
- Gas leak of ceramic paste results in lower OCV

## Summary

- Assembly of the glass carrier, reformer and micro-SOFC chip works.
- The heater was able to heat up the assembly till the self sustained reaction of the reformer sets in.
- Further heating was achieved by increasing the flow of butane and air.
- Theoretical OCV and a maximum power density of about 50 mW/cm<sup>2</sup> at 565 ° C was achieved.



## Outlook

- Excess of water results in unstable current-voltage curve.
- Integration of more stable (and active) electrode materials in order to achieve a better stability and higher power density
  - Metal alloys: Pt-Y-Al
  - Ceramics: LSC, LSMC
- Cement paste starts to leak at  $550^{\circ}\text{C}$ , which resulted in an unstable temperature due to complete combustion of the fuel.
- Current collection of the membranes should be improved
  - On the chip with connection path
  - To the out side with wire bonding

## Acknowledgements

# Thank you for your attention!

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